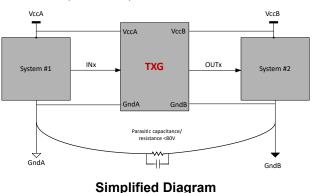


TXG804x-Q1 4-bit, ±80V Ground-Level Translator

1 Features

- Supports DC shifts up to ±80V
- AC Noise Rejection of 140V_{PP} up to 1MHz
- CMTI of 250V/µs
- ٠ Low Prop Delay (<5ns) and Ch-Ch Skew (0.35ns)
- Greater than 250Mbps
- Low power consumption (0.65mA per channel at 1Mbps, 1.8V)
- Fully configurable dual-rail design allows each port to operate from 1.71V to 5.5V
- 4, 2, 1 channel devices with multiple configurations will be available
- Two device variants:
 - TXG8041-Q1: 3 forward, 1 reverse
 - TXG8042-Q1: 2 forward, 2 reverse
- Supports V_{CC} disconnect feature (I/Os are forced into high-Z)
- Schmitt-trigger inputs allows for slow and noisy signals
- Inputs with integrated static pull-down resistors prevent channels from floating
- Operating temperature from -40°C to +125°C
- Latch-up performance exceeds 100mA per JESD 78, class II
 - ESD protection exceeds JESD 22
 - 4000V human-body model
 - 500V charged-device model
- Package options provided:
 - DYY (SOT-14)
 - DBQ (QSOP-16)



2 Applications

- **Electric Power Steering**
- Vehicle Control Unit
- Automotive Display
- Head Unit and Digital Cockpit

3 Description

The TXG804x-Q1 is a 4-bit, fixed direction, nongalvanic based voltage and ground-level translator that supports both logic-level shifting between 1.71V to 5.5V and ground-level shifting up to ±80V. Compared to traditional level shifters, the TXG804x-Q1 family solves the challenges of voltage translation across different ground levels. The Simplified Diagram shows a common use case where DC shift occurs between GNDA to GNDB due to parasitic resistance or capacitance.

 V_{CCA} is referenced to GNDA and V_{CCB} is referenced to GNDB. Ax pins are referenced to V_{CCA} logic level while Bx pins are referenced to V_{CCB} logic levels. Both A port and B port accept voltages from 1.71V to 5.5V. This device includes two enable pins that place the respective outputs in a high-impedance state when the OE pin is connected to GND or left floating. In the event of input power or signal loss, the output is default low when OE is High (refer to Table 7-1). The leakage between GNDA and GNDB is 70nA when V_{CC} to GND is shorted.

The TXG804x-Q1 device helps improve noise immunity and power sequencing across different ground domains while providing low power consumption, latency, and channel-to-channel skew. TXG804x-Q1 supresses noise levels of 140_{PP} up to 1MHz (Figure 7-4). This device supports multiple interfaces such as SPI, UART, GPIO, and I2S.

Package Information

	PART NUMBER	PACKAGE (1)	BODY SIZE (NOM)
	TXG8041-Q1 TXG8042-Q1	DYY (SOT-14)	4.20mm × 2.00mm
		DBQ (QSOP-16)	4.90mm x 3.90mm

For all available packages, see the orderable addendum at (1) the end of the data sheet.





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4 Pin Configuration and Functions

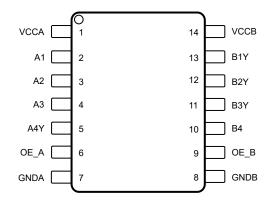


Figure 4-1. TXGx041DYY 14-Pin SOT Top View

Table 4-1. TXGx041 DYY Pin Functions

P	PIN		DESCRIPTION	
Name	TXGx041	- I/O	DESCRIPTION	
A1	2	I	Input A1. Referenced to V _{CCA}	
A2	3	I	Input A2. Referenced to V _{CCA}	
A3	4	I	Input A3. Referenced to V _{CCA}	
A4Y	5	0	Output A4. Referenced to V _{CCA}	
B1Y	13	0	Output B1. Referenced to V _{CCB}	
B2Y	12	0	Output B2. Referenced to V _{CCB}	
B3Y	11	0	Output B3. Referenced to V _{CCB}	
B4	10	I	Input B4. Referenced to V _{CCB}	
OE_A	6	I	Active-High Output Enable (A side). Pull to GND to place all outputs in high- impedance mode.	
OE_B	9	I	Active-High Output Enable (B side). Pull to GND to place all outputs in high- impedance mode.	
V _{CCA}	V _{CCA} 1		A side supply voltage. $1.71V \le V_{CCA} \le 5.5V$	
V _{CCB} 14		_	B side supply voltage. $1.71V \le V_{CCB} \le 5.5V$	
GNDA	7	—	Ground reference for V _{CCA}	
GNDB 8		_	Ground reference for V _{CCB}	



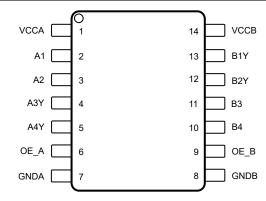




Table 4-2	TXGx042	DYY Pin	Functions
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PIN		I/O	DESCRIPTION	
Name	TXGx042		DESCRIPTION	
A1	2	I	Input A1. Referenced to V _{CCA}	
A2	3	I	Input A2. Referenced to V _{CCA}	
A3Y	4	0	Output A3. Referenced to V _{CCA}	
A4Y	5	0	Output A4. Referenced to V _{CCA}	
B1Y	13	0	Output B1. Referenced to V _{CCB}	
B2Y	12	0	Output B2. Referenced to V _{CCB}	
B3	11	I	Input B3. Referenced to V _{CCB}	
B4	10	I	Input B4. Referenced to V _{CCA}	
OE_A	OE_A 6		Active-High Output Enable (A side). Pull to GND to place all outputs in high- impedance mode.	
OE_B	9	I	Active-High Output Enable (B side). Pull to GND to place all outputs in high- impedance mode.	
V _{CCA} 1 — A side supply voltage. $1.71V \le V_{CC}$		A side supply voltage. $1.71V \le V_{CCA} \le 5.5V$		
V _{CCB} 14 — B side supply voltage. 1.71V ≤ V		_	B side supply voltage. $1.71V \le V_{CCB} \le 5.5V$	
GNDA 7		_	Ground reference for V _{CCA}	
GNDB	8	_	Ground reference for V _{CCB}	



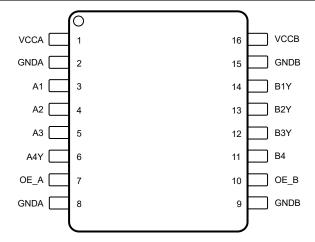




Table 4-3. TXGx041 DBQ Pin Functions

PI	PIN		DESCRIPTION	
Name	TXGx041	I/O	DESCRIPTION	
A1	3	I	Input A1. Referenced to V _{CCA}	
A2	4	I	Input A2. Referenced to V _{CCA}	
A3	5	I	Input A3. Referenced to V _{CCA}	
A4Y	6	0	Output A4. Referenced to V _{CCA}	
B1Y	14	0	Output B1. Referenced to V _{CCB}	
B2Y	13	0	Output B2. Referenced to V _{CCB}	
B3Y	12	0	Output B3. Referenced to V _{CCB}	
B4	11	I	Input B4. Referenced to V _{CCB}	
OE_A	7	I	Active-High Output Enable (A side). Pull to GND to place all outputs in high- impedance mode.	
OE_B	10	I	Active-High Output Enable (B side). Pull to GND to place all outputs in high- impedance mode.	
V _{CCA}	V _{CCA} 1		A side supply voltage. $1.71V \le V_{CCA} \le 5.5V$	
V _{CCB} 16		_	B side supply voltage. $1.71V \le V_{CCB} \le 5.5V$	
GNDA	2, 8	_	Ground reference for V _{CCA}	
GNDB 9, 15			Ground reference for V _{CCB}	



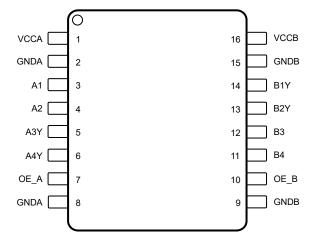




Table 4-4. TXGx042 DBQ Pin Functions

PIN	PIN Name TXGx042		DESCRIPTION
Name			DESCRIPTION
A1	3	I	Input A1. Referenced to V _{CCA}
A2	4	I	Input A2. Referenced to V _{CCA}
A3Y	5	0	Output A3. Referenced to V _{CCA}
A4Y	6	0	Output A4. Referenced to V _{CCA}
B1Y	14	0	Output B1. Referenced to V _{CCB}
B2Y	13	0	Output B2. Referenced to V _{CCB}
B3	12	I	Input B3. Referenced to V _{CCB}
B4	11	I	Input B4. Referenced to V _{CCB}
OE_A	7	I	Active-High Output Enable (A side). Pull to GND to place all outputs in high-impedance mode.
OE_B 10		I	Active-High Output Enable (B side). Pull to GND to place all outputs in high-impedance mode.
V _{CCA}	1 —		A side supply voltage. 1.71V $\leq V_{CCA} \leq 5.5V$
V _{CCB} 16 —		—	B side supply voltage. $1.71V \le V_{CCB} \le 5.5V$
GNDA 2, 8		_	Ground reference for V _{CCA}
GNDB 9, 15		—	Ground reference for V _{CCB}



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CCA} to V _{GNDA}	Supply voltage A to Ground voltage A	х	-0.5	6.5	V
V_{CCB} to V_{GNDB}	Supply voltage B to Ground voltage B		-0.5	6.5	V
V _{GNDA} to V _{GNDB}	Voltage between GNDA and GNDB		-82	82	V
		I/O Ports (A Port) to V _{GNDA}	-0.5	6.5	V
VI	Input Voltage ⁽²⁾	I/O Ports (B Port) to V _{GNDB}	-0.5	6.5	V
		OE	-0.5	6.5	V
V	Voltage applied to any output in the high-impedance or power-off state ⁽²⁾	A Port to V _{GNDA}	-0.5	6.5	V
Vo		B Port to V _{GNDB}	-0.5	6.5	v
M	Voltage applied to any output in the high or low state ⁽²⁾ ⁽³⁾	A Port to V _{GNDA}	-0.5	6.5	V
Vo		B Port to V _{GNDB}	-0.5	6.5	v
I _{IK}	Input clamp current	V ₁ < 0	-20		mA
I _{OK}	Output clamp current	V _O < 0	-20		mA
I _O	Continuous output current		-16	16	mA
	Continuous current through V _{CCx} or G	-64	64	mA	
Tj	Junction Temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Section 5.1 may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Section 5.3 Exposure beyond the limits listed in Section 5.3 may affect device reliability.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 6.5V maximum if the output current rating is observed.

5.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	
V _(ESD)		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±500	V

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

			MIN	TYP MAX	UNIT
V _{CCA}	Supply voltage A - Relative to 0	GNDA	1.71	5.5	V
V _{CCB}	Supply voltage B - Relative to 0	GNDB	1.71	5.5	V
V _{GNDA} to V _{GNDB}	Voltage between GNDA and GI	NDB	-80	80	V
		V _{CCO} = 1.71V	-4.5		
1	High-level output current	V _{CCO} = 2.3V	-8		mA
I _{ОН}		V _{CCO} = 3V	-10		
		V _{CCO} = 4.5V	-12		
	Low-level output current	V _{CCO} = 1.71V		4.5	- mA
		V _{CCO} = 2.3V		8	
I _{OL}		V _{CCO} = 3V		10	
		V _{CCO} = 4.5V		12	
VI	Input voltage - Relative to GND	X	0	5.5	V
Vo	Output voltage - Relative to GN	IDx	0	V _{CCO}	V
T _A	Operating free-air temperature		-40	125	°C

(1) V_{CCI} is the V_{CC} associated with the input port.

(2) V_{CCO} is the V_{CC} associated with the output port.

(3) All control inputs and data I/Os of this device have weak pulldowns to ensure the line is not floating when undefined external to the device. The input leakage from these weak pulldowns is defined by the I_I specification indicated under Section 5.5

5.4 Thermal Information

		TXGx041 a	TXGx041 and TXGx042		
	THERMAL METRIC (1)	DYY (SOT)	DBQ (QSOP)	UNIT	
		14 PINS	16 PINS		
R _{0JA}	Junction-to-ambient thermal resistance	128.4	143.1	°C/W	
R _{0JC(top)}	Junction-to-case (top) thermal resistance	52.4	82.3	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	58.5	46.9	°C/W	
Y _{JT}	Junction-to-top characterization parameter	2.7	1.2	°C/W	
Y _{JB}	Junction-to-board characterization parameter	51.9	81.9	°C/W	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

						ting free-a erature (T		
	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	-40°0	C to 125°C	;	UNIT
					MIN	TYP	MAX	
		I _{OH} =4.5mA	1.71V	1.71V	1.5			
,	High-level output	I _{OH} = -8mA	2.3V	2.3V	2.0			V
V _{OH}	voltage ⁽³⁾	I _{OH} = -10mA	3V	3V	2.6			V
		$I_{OH} = -12mA$	4.5V	4.5V	4.0			
		I _{OL} = 4.5mA	1.71V	1.71V			0.18	
,	Low-level output	I _{OL} = 8mA	2.3V	2.3V			0.33	
V _{OL}	voltage ⁽⁴⁾	I _{OL} = 10mA	3V	3V			0.41	V
		I _{OL} = 12mA	4.5V	4.5V			0.49	
			1.71V	1.71V			1.14	
	Positive-going	Data Inputs	2.3V	2.3V			1.42	
V _{T+}	input-threshold	(Ax, Bx)	3V	3V			1.74	V
	voltage	(Referenced to V _{CCI})	4.5V	4.5V			2.47	
			5.5V	5.5V			2.97	
			1.71V	1.71V			1.12	
	Positive-going		2.3V	2.3V			1.42	
/ _{T+} input-threshold voltage	OE (Referenced to V _{CCA} or V _{CCB)}	3V	3V			1.73	V	
	voltage	(Referenced to v _{CCA} of v _{CCB})	4.5V	4.5V			2.47	-
			5.5V	5.5V			2.94	
			1.71V	1.71V	0.52			
	Negative-going	Data Inputs	2.3V	2.3V	0.76			
V _{T-}	input-threshold	(Ax, Bx)	3V	3V	1.09			V
-	voltage	(Referenced to V _{CCI})	4.5V	4.5V	1.77			
			5.5V	5.5V	2.28			
			1.71V	1.71V	0.46			
	Negativo going		2.3V	2.3V	0.76			
V _{T-}	Negative-going input-threshold	OE (Deferenced to)(3V	3V	1.04			V
	voltage	(Referenced to V_{CCA} or V_{CCB})	4.5V	4.5V	1.86			
			5.5V	5.5V	2.5			
			1.71V	1.71V	0.24		0.54	
	Input throohold	Data Innuta	2.3V	2.3V	0.29		0.60	
ΔV _T	Input-threshold hysteresis	Data Inputs (Ax, Bx)	3V	3V	0.33		0.54	V
-	$(V_{T+} - V_{T-})$	(Referenced to V _{CCI})	4.5V	4.5V	0.38		0.82	
			5.5V	5.5V	0.37		0.96	
			1.71V	1.71V	0.24		0.45	
	Innest threads and		2.3V	2.3V	0.28		0.58	
ΔV _T	Input-threshold hysteresis	OE (Deferenced to)/ or)/	3V	3V	0.32		0.54	v
•	$(V_{T+} - V_{T-})$	(Referenced to V_{CCA} or V_{CCB})	4.5V	4.5V	0.35		0.58	
			5.5V	5.5V	0.39		0.62	
1	Input leakage current	Data Inputs (Ax, Bx) V _I = V _{CCI} or GND	1.71V – 5.5V	1.71V – 5.5V			1.6	μA

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over operating free-air temperature range (unless otherwise noted)⁽¹⁾ (2)

PARAMETER		TEST CONDITIONS	V _{CCA}	V _{CCB}	tempe	ting free- erature (T C to 125°	「₄)	UNIT
					MIN	TYP	MAX	
	Floating supply	A Port or B Port	Floating ⁽⁵⁾	0V - 5.5V	-2.5		2.5	
I _{off-float}	Partial power down current	$V_{I} = GND$	0V - 5.5V	Floating ⁽⁵⁾	-2.5		2.5	μA
lo	Tri-state output Output current	A or B Port: V _I = V _{CCA} or V _{GNDA} OE = GND	1.71V – 5.5V	1.1V – 5.5V	-5		5	μA
Ci	Control Input Capacitance	$V_{I} = 3.3 V \text{ or } V_{GNDA}$	3.3V	3.3V		2		pF
C _{io}	Data I/O Capacitance	OE = GND, V _O = 1.71V DC +1MHz -16dBm sine wave	3.3V	3.3V		5		pF
C _{GND}	Cap between grounds	All channels combined $(V_{CC}$ both sides are powered on)					49	pF
	grounds	All channels combined (V _{CC} to GND shorted)					54	pF
		All channels combined (V _{CC} to GND shorted)	1.71V – 5.5V	1.71V – 5.5V		70		nA
Leakage	Current Leakage between GndA to GndB	All channels combined (V _{CC} both sides are powered on and inputs are all low)	1.71V – 5.5V	1.71V – 5.5V		70		nA
		All channels combined (V _{CC} both sides are powered on and inputs are all high)	1.71V – 5.5V	1.71V – 5.5V		33		μA
СМТІ	Common Mode Transient Immunity	Input toggling at 100Mbps Ground shift up to 80V	1.71V – 5.5V	1.71V – 5.5V			250	V/µs
	Positive-Going	A Supply	1.71V – 5.5V				1.55	
V _{UVLO+}	Undervoltage Lockout Voltage	B Supply		1.71V – 5.5V			1.55	V
	Negative-Going	A Supply	1.71V – 5.5V		1.36			
V _{UVLO-}	Undervoltage Lockout Voltage	B Supply		1.71V – 5.5V	1.36			V
~	Undervoltage	A Supply	1.71V – 5.5V		36		147	mV
V _{UVLO_Hys}	Lockout Hysteresis	B Supply		1.71V – 5.5V	36		147	IIIV

 V_{CCI} is the V_{CC} associated with the input port and referenced to GND_A V_{CCO} is the V_{CC} associated with the output port and referenced to GND_B (1) (2) (3) (4) (5)

Tested at $V_1 = V_{T+(MAX)}$ Tested at $V_1 = V_{T-(MIN)}$ Floating is defined as a node that is both not actively driven by an external device and has leakage not exceeding 10nA



5.6 Supply Current

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

	PARAMETER				Opera tempe	ting free-air erature (T _A)	UNIT
	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	-40°	C to 125°C	
					MIN	TYP MAX	
TXGx041							
			1.71V – 5.5V	1.71V – 5.5V	546	1220	
		$V_I = V_{CCI}$ or GND $I_O = 0$	0V	5.5V	-3	13	
I _{CCA}	V _{CCA} supply current		5.5V	0V	509	1050	μA
		$V_1 = GND$ $I_0 = 0$	5.5V	Floating ⁽³⁾	509	1050	
			1.71V – 5.5V	1.71V – 5.5V	750	1836	
		$V_{I} = V_{CCI} \text{ or } GND$ $I_{O} = 0$	0V	5.5V	654	1350	
I _{CCB} V _{CCB} sut	V _{CCB} supply current	.0 0	5.5V	0V	-3	36	μA
		$V_1 = GND$ $I_0 = 0$	Floating ⁽³⁾	5.5V	656	1350	
			1.8V	1.8V	1.9	3.1	
	Supply Current Dischle	EN = 0	2.5V	2.5V	1.9	3.1	mA
I _{CCA} + I _{CCB}	Supply Current - Disable	EN - 0	3.3V	3.3V	2.0	3.1	
			5V	5V	2.1	3.3	
			1.8V	1.8V	1	2.65	
		× - ×	2.5V	2.5V	1.3	2.7	
		V _I = V _{CCI}	3.3V	3.3V	1.3	2.8	
	Supply Current DC Signal		5V	5V	1.4	3.1	
I _{CCA} + I _{CCB}	Supply Current - DC Signal		1.8V	1.8V	1.2	2.7	mA
		V _I = GND	2.5V	2.5V	1.3	2.7	
			3.3V	3.3V	1.3	2.8	
			5V	5V	1.4	3.1	

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over operating free-air temperature range (unless otherwise noted) $^{(1)}$ ⁽²⁾

						ting free-air erature (T _A)	
	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	-40°	C to 125°C	UNIT
					MIN	TYP MAX	
			1.8V	1.8V	1.5	2.6	
		All channels switching with square wave clock input;	2.5V	2.5V	1.6	2.7	
		$C_L = 15 pF$, 1Mbps	3.3V	3.3V	1.6	2.8	
			5V	5V	1.9	3.3	
			1.8V	1.8V	9.2	12.1	
		All channels switching with square wave	2.5V	2.5V	10.8	14	
I _{CCA} + I _{CCB}	Supply Current - AC Signal	clock input; C _L = 15pF, 50Mbps	3.3V	3.3V	12.4	16.2	mA
			5V	5V	17.6	20.6	
			1.8V	1.8V	16.5	20.1	
		All channels switching with square wave	2.5V	2.5V	20.2	24.7	
		clock input; C _L = 15pF, 100Mbps	3.3V	3.3V	24.1	29	
			5V	5V	35	38	
TXGx042	I						
			1.71V – 5.5V	1.71V – 5.5V	547	1365	
		$V_{I} = V_{CCI}$ or GND $I_{O} = 0$	0V	5.5V	-2.6	25	μΑ
I _{CCA}	V _{CCA} supply current	1 ₀ - 0	5.5V	0V	625	1052	
		V _I = GND I _O = 0	5.5V	Floating ⁽³⁾	625	1052	
			1.71V – 5.5V	1.71V – 5.5V	753	1692	
		$V_{I} = V_{CCI} \text{ or GND}$ $I_{O} = 0$	0V	5.5V	819	1380	
I _{CCB}	I _{CCB} V _{CCB} supply current	1 ₀ - 0	5.5V	0V	-2.4	25	μA
		$V_I = GND$ $I_O = 0$	Floating ⁽³⁾	5.5 V	823	1380	
			1.8V	1.8V	1.9	3.1	
		2.5V	2.5V	1.9	3.1		
I _{CCA} + I _{CCB}	Supply Current - Disable	EN = 0	3.3V	3.3V	2	3.1	mA
	5.3 5V	5V	5V	2.1	3.3		



over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

						ting free-air erature (T _A)	
	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	-40°0	C to 125°C	UNIT
					MIN	TYP MAX	
			1.8V	1.8V	1.2	2.7	
		$V_{I} = V_{CCI}$	2.5V	2.5V	1.3	2.6	
			3.3V	3.3V	1.3	2.7	
 +	Supply Current - DC Signal		5V	5V	1.4	3.1	mA
I _{CCA} + I _{CCB}	Supply Current - DC Signal		1.8V	1.8V	1.2	2.7	
		V _I = GND	2.5V	2.5V	1.3	2.6	
			3.3V	3.3V	1.3	2.7	
			5V	5V	1.4	3.1	
			1.8V	1.8V	1.5	2.6	
		All channels switching with square wave clock input;	2.5V	2.5V	1.6	2.7	
		$C_L = 15$ pF, 1Mbps	3.3V	3.3V	1.6	2.8	
			5V	5V	1.9	3.3	
			1.8V	1.8V	9.5	12.9	
I _{CCA} + I _{CCB}	Supply Current - AC Signal	All channels switching with square wave clock input;	2.5V	2.5V	10.6	13.9	mA
		$C_L = 15$ pF, 50 Mbps	3.3V	3.3V	12.9	15.9	ШA
			5V	5V	17.7	20.8	
			1.8V	1.8V	16.5	20	
		All channels switching with square wave clock input;	2.5V	2.5V	20.5	25.2	
		$C_L = 15$ pF, 100 Mbps	3.3V	3.3V	24.4	28.7	
			5V	5V	34.9	38.4	

 V_{CCI} is the V_{CC} associated with the input port (1)

(2)

 V_{CCO} is the V_{CC} associated with the output port Floating is defined as a node that is both not actively driven by an external device and has leakage not exceeding 10nA (3)



5.7 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15V$

									B-Port Supply	Voltage	(V _{CCB})			
I	PARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	5 ± 0.15V	2	.5 ± 0.2V	3.	3 ± 0.3V	5	.0 ± 0.5V	
						MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MA	X MIN	TYP MAX	1
			A	В	-40°C to 85°C	3	7.4	3	7.5	3.1	7.	5 3.1	7.9	
	Propagation delay	1Mbps all 4 channels	A	В	-40°C to 125°C	3	7.8	3	7.8	3.1	7.	9 3.1	8.4	1
t _{pd}	Propagation delay	toggling	В	A	-40°C to 85°C	3	7.4	2.8	5.8	2.8	5.	2 2.8	4.9	ns
			В	A	-40°C to 125°C	3	7.8	2.8	6.1	2.8	5.	5 2.8	5.2	1
			OE	A	-40°C to 85°C	16.1	35	16.1	35	16.1	3	5 16.1	35	
	Disable time		OE	A	-40°C to 125°C	16.1	35.6	16.1	35.5	16.1	35.	6 16.1	35.6	1
t _{dis}	Disable time		OE	В	-40°C to 85°C	17.6	40.9	12.6	28.2	14.7	27.	4 10	18.8	ns
			OE	В	-40°C to 125°C	17.6	42	12.6	29.1	14.7	2	8 10	19.3	1
			OE	A	-40°C to 85°C	5.4	18.1	5.4	18.1	5.4	18.	1 5.4	18.1	
	En abla tima		OE	A	-40°C to 125°C	5.4	18.9	5.4	18.8	5.4	18.	9 5.4	18.8	
t _{en}	Enable time		OE	В	-40°C to 85°C	7.5	26.5	5.5	15.3	4.5	1	1 3.8	7.9	ns
		OE	В	-40°C to 125°C	7.9	27.5	5.5	16.3	4.5	11.	8 3.8	8.4	1	
		A	В	-40°C to 85°C	0.7	1.5	0.6	1.4	0.6	1.	3 0.5	1.2		
	Pulse width	Itabi - taibi	A	В	-40°C to 125°C	0.7	1.5	0.6	1.4	0.6	1.	3 0.5	1.2	
PWD	distortion		В	A	-40°C to 85°C	0.7	1.5	0.6	1.4	0.6	1.	3 0.5	1.2	ns
			В	A	-40°C to 125°C	0.7	1.5	0.6	1.4	0.6	1.	3 0.5	1.2	1
			A	В	-40°C to 85°C	0.6	1.1	0.5	1.2	0.5	1.	5 0.6	1.8	
	Output signal rise		A	В	-40°C to 125°C	0.6	1.3	0.5	1.5	0.5	1.	6 0.6	1.9	
t _r	time		В	A	-40°C to 85°C	0.5	0.9	0.5	1	0.5	0.	9 0.5	0.9	ns
			В	A	-40°C to 125°C	0.5	1	0.5	1.1	0.5		1 0.5	1.1	1
			A	В	-40°C to 85°C	0.5	1.3	0.5	1.6	0.5	1.	6 0.6	1.9	
tf	Output signal fall		A	В	-40°C to 125°C	0.5	1.6	0.5	1.8	0.5	1.	9 0.6	2.2	1
ti	time		В	A	-40°C to 85°C	0.5	1.1	0.5	1.1	0.5	1.	1 0.5	1.1	ns
			В	A	-40°C to 125°C	0.5	1.4	0.5	1.5	0.5	1.	4 0.5	1.4	1
	Default output	Measured from the			-40°C to 85°C		8.4		8.3		8.	2	8	
t _{DO}	delay time from input power loss	time V _{CC} goes below 1.36V			-40°C to 125°C		8.4		8.3		8.	2	8	μs
	Time from ULVO				-40°C to 85°C		66.8		66.8		66.	8	66.9	
t _{PU}	to valid output data				-40°C to 125°C		66.8		66.8		66.	8	66.9	μs



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5.8 Switching Characteristics, V_{CCA} = 2.5 \pm 0.2V

									B-Port Supply	Voltage	(V _{CCB})					
1	PARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	3 ± 0.15V	2	.5 ± 0.2V	3.	.3 ± 0.3\	1	5.	0 ± 0.5V		UNIT
						MIN	TYP MA	(MIN	TYP MAX	MIN	TYP	MAX	MIN	TYP N	AX	
			A	В	-40°C to 85°C	2.9	5.	9 2.9	5.9	2.9		6	3		6.2	
	Dranagation dology	1Mbps all 4 channels	A	В	-40°C to 125°C	2.9	6.	1 2.9	6.2	2.9		6.3	3		6.6	
t _{pd}	Propagation delay	toggling	В	A	-40°C to 85°C	3	7.	4 2.9	5.9	2.8		5.2	2.8		5	ns
			В	A	-40°C to 125°C	3	7.	3 2.9	6.2	2.8		5.6	2.8		5.4	
			OE	A	-40°C to 85°C	11.6	24.	7 11.6	24.7	11.6		24.7	11.6	2	4.7	
	Dischle time		OE	A	-40°C to 125°C	11.6	25.	2 11.6	25.2	11.6		25.2	11.6	2	5.2	
t _{dis}	Disable time		OE	В	-40°C to 85°C	17.6	40.	9 12.6	28.3	14.7		27.4	10.1		8.8	ns
			OE	В	-40°C to 125°C	17.6	41.	9 12.6	29.1	14.7		28	10.1		9.3	
			OE	A	-40°C to 85°C	3.8	10.	3.8	10.9	3.8		10.9	3.8		0.9	
	En abla tima		OE	A	-40°C to 125°C	3.8	11.	3.8	11.6	3.8		11.6	3.8		1.6	
en	Enable time		OE	В	-40°C to 85°C	7.5	26.	5 5.5	15.3	4.5		11	3.8		7.8	ns
		OE	В	-40°C to 125°C	7.9	27.	5 5.5	16.3	4.5		11.8	3.8		8.4		
			A	В	-40°C to 85°C	0.1	0.	6 0.1	0.57	0.002		0.56	0.002	(0.48	
	Pulse width	t _{phi} - t _{pih}	A	В	-40°C to 125°C	0.1	0.	6 0.1	0.57	0.002		0.56	0.002	(.48	- ns
PWD	distortion		В	A	-40°C to 85°C	0.1	0.	6 0.1	0.57	0.002		0.56	0.002	(.48	ns
			В	A	-40°C to 125°C	0.1	0.	6 0.1	0.57	0.002		0.56	0.002	(.48	
			A	В	-40°C to 85°C	0.6	1.	1 0.5	1.2	0.5		1.5	0.6		1.8	
	Output signal rise		A	В	-40°C to 125°C	0.6	1.	3 0.5	1.4	0.5		1.7	0.6		1.9	
۰r	time		В	A	-40°C to 85°C	0.5		1 0.5	1	0.5		1	0.5		1	ns
			В	A	-40°C to 125°C	0.5	1.	1 0.5	1.2	0.5		1.2	0.5		1.1	
			A	В	-40°C to 85°C	0.5	1.	2 0.5	1.5	0.5		1.7	0.5		1.9	
f	Output signal fall time		A	В	-40°C to 125°C	0.5	1.	6 0.5	1.7	0.5		1.8	0.5		2.1	
u			В	A	-40°C to 85°C	0.5	1.	3 0.5	1.3	0.5		1.4	0.5		1.3	ns
			В	A	-40°C to 125°C	0.5	1.	5 0.5	1.5	0.5		1.5	0.5		1.6	
	Default output	Measured from the			-40°C to 85°C		8.	1	8.1			8			7.8	
ро	delay time from input power loss	time V _{CC} goes below 1.36V			-40°C to 125°C		8.	1	8.1			8			7.8	μs
	Time from ULVO				-40°C to 85°C		71.	3	71.3			71.3		7	1.3	
t _{PU}	to valid output data				-40°C to 125°C		71.	3	71.3			71.3		1	1.3	μs



5.9 Switching Characteristics, V_{CCA} = 3.3 \pm 0.3V

									В	-Port Supp	y Volta	ge (V	ссв)					
I	PARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	± 0.15V		2.5	5 ± 0.2V		3.3 ±	: 0.3V		5.	0 ± 0.5V		
						MIN	TYP MA	X I	MIN	TYP MA	х мі	N 1	ГҮР	MAX	MIN	TYP	MAX	
			A	В	-40°C to 85°C	2.9	5	2	2.9	5	3 2	8		5.4	3		5.7	
•	Dranagation dalay	1Mbps all 4 channels	A	В	-40°C to 125°C	2.9	5	5	2.9	5	6 2	8		5.8	3		6.1	
t _{pd}	Propagation delay	toggling	В	A	-40°C to 85°C	3	7	5	2.9	5	9 2	8		5.3	2.8		5.1	ns
			В	A	-40°C to 125°C	3	7	9	2.9	6	3 2	8		5.7	2.8		5.5	
			OE	A	-40°C to 85°C	13.9	25	3 ´	13.8	25	3 13	8		25.3	13.8		25.3	
	Disable time		OE	A	-40°C to 125°C	13.9	25	7 1	13.8	25	7 13	8		25.7	13.8		25.7	
t _{dis}	Disable time		OE	В	-40°C to 85°C	17.6	40	9 1	12.6	28	2 14	7		27.4	10.1		18.8	ns
			OE	В	-40°C to 125°C	17.6	41	9 1	12.6	2	9 14	7		28	10.1		19.3	
			OE	A	-40°C to 85°C	3		8	3.1		8 3	1		8	3		8	
	En altitudina a		OE	A	-40°C to 125°C	3	8	5	3.1	8	5 3	1		8.6	3		8.5	
t _{en}	Enable time		OE	В	-40°C to 85°C	7.5	26	5	5.5	15	3 4	5		11	3.8		7.8	ns
		OE	В	-40°C to 125°C	8	27	5	5.5	16	3 4	5		11.8	3.8		8.4		
			A	В	-40°C to 85°C	0.006	0.3	7 0.	.002	0.3	7 0.00	1		0.34	0		0.36	
	Pulse width		A	В	-40°C to 125°C	0.006	0.3	7 0.	.002	0.3	7 0.00	1		0.34	0		0.36	
PWD	distortion	t _{phl} - t _{plh}	В	A	-40°C to 85°C	0.006	0.3	7 0.	.002	0.3	7 0.00	1		0.34	0		0.36	ns
			В	A	-40°C to 125°C	0.006	0.3	7 0.	.002	0.3	7 0.00	1		0.34	0		0.36	
			A	В	-40°C to 85°C	0.6	1.	1	0.6	1.	2 0	5		1.5	0.6		1.8	
	Output signal rise		A	В	-40°C to 125°C	0.6	1.	3	0.6	1	5 0	5		1.7	0.6		1.9	
t _r	time		В	A	-40°C to 85°C	0.6	1.	1	0.6	1	2 0	5		1.5	0.6		1.8	ns
			В	A	-40°C to 125°C	0.6	1.	3	0.6	1	5 0	5		1.7	0.6		1.9	
			A	В	-40°C to 85°C	0.5	1.	2	0.5	1.	6 0	5		1.6	0.6		1.9	
	Output signal fall		A	В	-40°C to 125°C	0.5	1.	7	0.5	1.	7 0	5		1.8	0.6		2.1	
π	f time		В	A	-40°C to 85°C	0.5	1.	4	0.5	1	5 0	5		1.4	0.5		1.5	ns
			В	A	-40°C to 125°C	0.5	1.	7	0.5	1	7 0	5		1.7	0.5		1.6	
	Default output	Measured from the			-40°C to 85°C			8		7.	9			7.9			7.7	μs
t _{DO}	delay time from input power loss	time V _{CC} goes below 1.36V			-40°C to 125°C			8		7.	9			7.9			7.7	μs
	Time from ULVO				-40°C to 85°C		79	1		79	1			79.1			79.1	μs
t _{PU}	to valid output data				-40°C to 125°C		79	1		79	1			79.1			79.1	μs



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5.10 Switching Characteristics, V_{CCA} = 5.0 \pm 0.5V

								1	B-Port Supply	Voltage	(V _{CCB})					
F	PARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	5 ± 0.15V	2.	5 ± 0.2V	3.	3 ± 0.3V	5.	0 ± 0.5V			
						MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	1		
			A	В	-40°C to 85°C	2.8	5	2.8	5	2.9	5.2	2.9	5.5			
	Propagation delay	1Mbps all 4 channels	A	В	-40°C to 125°C	2.8	5.3	2.8	5.3	2.9	5.6	2.9	5.9			
pd	Propagation delay	toggling	В	A	-40°C to 85°C	3.1	7.8	3	6.3	2.9	5.7	2.8	5.6	- ns		
			В	A	-40°C to 125°C	3.1	8.3	3	6.6	2.9	6.1	2.8	5.8	1		
			OE	A	-40°C to 85°C	9.4	17.4	9.4	17.4	9.4	17.4	9.4	17.4			
	Disable time		OE	A	-40°C to 125°C	9.4	17.7	9.4	17.7	9.4	17.7	9.4	17.7	1		
dis	Disable time		OE	В	-40°C to 85°C	17.7	40.9	12.6	28.3	14.7	27.4	10.1	18.8	- ns		
			OE	В	-40°C to 125°C	17.7	41.9	12.6	29.1	14.7	28	10.1	19.4	1		
			OE	A	-40°C to 85°C	2.5	5.9	2.5	5.9	2.5	5.9	2.5	5.9			
	En alt la time a		OE	A	-40°C to 125°C	2.5	6.3	2.5	6.3	2.5	6.3	2.5	6.3			
en	Enable time		OE	В	-40°C to 85°C	7.5	26.5	5.5	15.3	4.5	11	3.8	7.8	- ns		
			OE	В	-40°C to 125°C	8	27.5	5.5	16.3	4.5	11.8	3.8	8.4	1		
			A	В	-40°C to 85°C	0	0.2	0	0.3	0.003	0.4	0.011	0.7			
	Pulse width	h t _{phi} - t _{pih}	A	В	-40°C to 125°C	0	0.2	0	0.3	0.003	0.4	0.011	0.7			
PWD	distortion		В	A	-40°C to 85°C	0	0.2	0	0.3	0.003	0.4	0.011	0.7	- n:		
			В	A	-40°C to 125°C	0	0.2	0	0.3	0.003	0.4	0.011	0.7	1		
			A	в	-40°C to 85°C	0.6	1.1	0.5	1.1	0.5	1.6	0.6	1.8			
	Output signal rise		A	В	-40°C to 125°C	0.6	1.3	0.5	1.5	0.5	1.7	0.6	1.9			
r	time		В	A	-40°C to 85°C	0.5	1.6	0.5	1.6	0.5	1.7	0.5	1.7	- n:		
			В	A	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.5	1.7	1		
			A	В	-40°C to 85°C	0.5	1.4	0.4	1.6	0.5	1.8	0.6	1.9			
-	Output signal fall		A	В	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.2	1		
f	time				В	A	-40°C to 85°C	0.5	1.4	0.5	1.6	0.5	1.8	0.6	1.9	- ns
			В	A	-40°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.2	1		
	Default output	Measured from the			-40°C to 85°C		7.9		7.8		7.7		7.6			
00	delay time from input power loss	time V _{CC} goes below 1.36V			-40°C to 125°C		7.9		7.8		7.7		7.6	μ		
	Time from ULVO				-40°C to 85°C		98.3		98.3		98.3		98.3			
PU	to valid output data				-40°C to 125°C		98.3		98.3		98.3		98.3	μs		



5.11 Switching Characteristics: T_{sk}, T_{MAX}

over operating free-air temperature range (unless otherwise noted)

			Ver		Opera tempe			
PARAMETER	TEST CON	DITIONS	V _{CCI}	V _{cco}	-40°C	C to 125°C	;	UNIT
					MIN	TYP	MAX	
	50% Duty Cycle Input		1.65V - 1.95V	1.65V - 1.95V	264			Mbps
T Maximum Data Data	One channel switching	No Translation	2.3V - 2.7V	2.3V - 2.7V	264			Mbps
T _{MAX} - Maximum Data Rate	20% of pulse > $0.7*V_{CCO}$	NO Translation	3.0V - 3.6V	3.0V - 3.6V	176			Mbps
	20% of pulse < 0.3^*V_{CCO}		4.5V - 5.5V	4.5V - 5.5V	176			Mbps
			1.65V - 1.95V	2.3V - 2.7V	264			Mbps
	50% Duty Cycle Input		1.65V - 1.95V	3.0V - 3.6V	264			Mbps
T Mauinaum Data Data	One channel switching 20% of pulse > $0.7*V_{CCO}$ 20% of pulse < $0.3*V_{CCO}$	Lin Tropolation	1.65V - 1.95V	4.5V - 5.5V	264			Mbps
T _{MAX} - Maximum Data Rate		Up Translation	2.3V - 2.7V	3.0V - 3.6V	264			Mbps
			2.3V - 2.7V	4.5V - 5.5V	220			Mbps
			3.0V - 3.6V	4.5V - 5.5V	176			Mbps
			2.3V - 2.7V	1.65V - 1.95V	285			Mbps
		Down Translation	3.0V - 3.6V	2.3V - 2.7V	220			Mbps
T. Maximum Data Data	50% Duty Cycle Input One channel switching		3.0V - 3.6V	1.65V - 1.95V	220			Mbps
T _{MAX} - Maximum Data Rate	20% of pulse > $0.7*V_{CCO}$		4.5V - 5.5V	3.0V - 3.6V	176			Mbps
	20% of pulse < 0.3^*V_{CCO}		4.5V - 5.5V	2.3V - 2.7V	220			Mbps
			4.5V - 5.5V	1.65V - 1.95V	220			Mbps
	Timing allow between any		1.65V - 1.95V	1.65V - 1.95V			0.35	ns
	Timing skew between any switching outputs on the	N. Translation	2.3V - 2.7V	2.3V - 2.7V			0.35	ns
t _{sk} - Output skew	rising or falling edge (same	No Translation	3.0V - 3.6V	3.0V - 3.6V			0.35	ns
	direction channels)		4.5V - 5.5V	4.5V - 5.5V			0.35	ns
			1.65V - 1.95V	2.3V - 2.7V			0.35	ns
	Timina altauthaturan arres		1.65V - 1.95V	3.0V - 3.6V			0.35	ns
	Timing skew between any switching outputs on the	Lin Translation	1.65V - 1.95V	4.5V - 5.5V			0.35	ns
t _{sk} - Output skew	rising or falling edge (same	Up Translation	2.3V - 2.7V	3.0V - 3.6V			0.35	ns
	direction channels)		2.3V - 2.7V	4.5V - 5.5V			0.35	ns
			3.0V - 3.6V	4.5V - 5.5V			0.35	ns



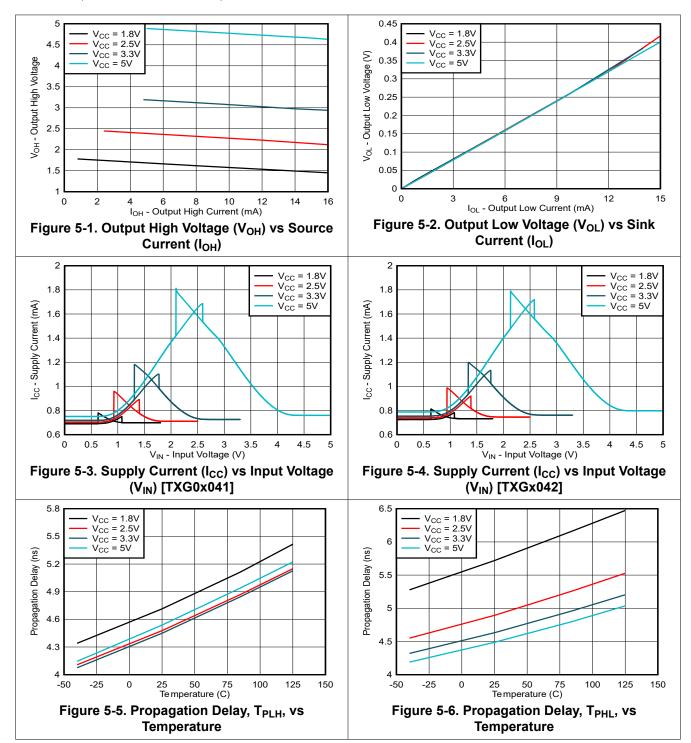
over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V _{CCI}		Operating free-air temperature (T _A)		UNIT	
				V _{cco}	-40°C to 125°C			
					MIN	TYP	MAX	
	Timing skew between any switching outputs on the rising or falling edge (same direction channels)	Down Translation	2.3V - 2.7V	1.65V - 1.95V			0.35	ns
t _{sk} - Output skew			3.0V - 3.6V	2.3V - 2.7V			0.35	ns
			3.0V - 3.6V	1.65V - 1.95V			0.35	ns
			4.5V - 5.5V	3.0V - 3.6V			0.35	ns
			4.5V - 5.5V	2.3V - 2.7V			0.35	ns
			4.5V - 5.5V	1.65V - 1.95V			0.35	ns

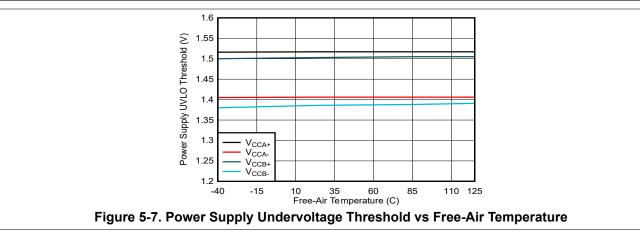


5.12 Typical Characteristics

 $T_A = 25^{\circ}C$ (unless otherwise noted)







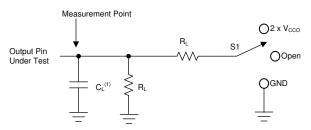


6 Parameter Measurement Information

6.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, generators supply all input pulses that have the following characteristics:

- f = 1MHz
- $Z_{O} = 50\Omega$ $\Delta t/\Delta V \le 1$ ns/V

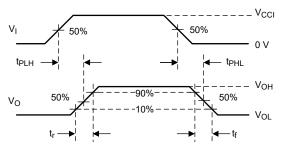


C_L includes probe and jig capacitance. Α.

Figure 6-1. Load Circuit

Table 6-1. Load Circuit Conditions

	Parameter	V _{cco}	RL	CL	S ₁	V _{TP}
t _{pd}	Propagation (delay) time	1.71V – 5.5V	10kΩ	15pF	Open	N/A
t _{en} , t _{dis} E	Enable time, disable time	1.71V – 2.7V	10kΩ	15pF	2 × V _{CCO}	0.15V
	Enable line, disable line	3.0V – 5.5V	10kΩ	15pF	2 × V _{CCO}	0.3V
t _{en} , t _{dis} Er	Table time, disable time	1.71V – 2.7V	10kΩ	15pF	GND	0.15V
	Enable time, disable time	3.0V – 5.5V	10kΩ	15pF	GND	0.3V

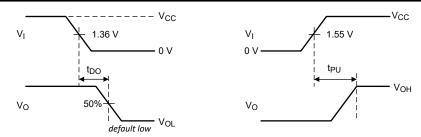


 V_{CCI} is the supply pin associated with the input port. 1.

 V_{OH} and V_{OL} are typical output voltage levels that occur with specified RL, CL, and S1 2.

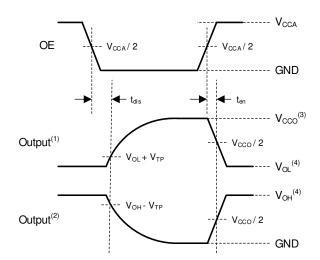
Figure 6-2. Switching Characteristics Voltage Waveforms





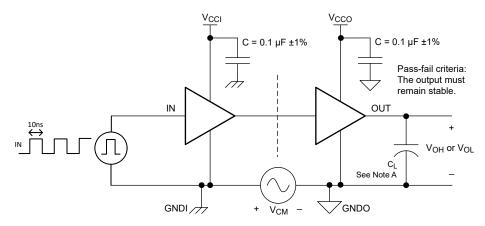
- 1. V_{CCI} is the supply pin associated with the input port.
- 2. V_{OH} and V_{OL} are typical output voltage levels that occur with specified R_L, C_L, and S₁

Figure 6-3. Default Output Delay Time & Time from UVLO to Valid Output Voltage Waveform



- 1. Output waveform on the condition that input is driven to a valid Logic Low.
- 2. Output waveform on the condition that input is driven to a valid Logic High.
- 3. V_{CCO} is the supply pin associated with the output port.
- 4. V_{OH} and V_{OL} are typical output voltage levels with specified R_L, C_L, and S₁.

Figure 6-4. Enable Time And Disable Time





1. $C_L = 15pF$ and includes instrumentation and fixture capacitance within ±20%.



7 Detailed Description

7.1 Overview

The TXG804x-Q1 is a 4-bit ground-level translator that uses two individually configurable power-supply rails which allows it to translate across two different power domains. The device is operational with V_{CCA} and V_{CCB} supplies as low as 1.71V and as high as 5.5V. The A port is designed to track V_{CCA} and the B port is designed to track V_{CCB} . In addition to I/O level shifting, this translator can support a difference of -80V to +80V between GNDA and GNDB. V_{CCA} is referenced to GNDA and V_{CCB} is referenced to GNDA.

The TXG804x-Q1 device is designed for asynchronous communication between data buses, and transmits data with fixed direction from the A bus to the B bus on some channels and from the B bus to the A bus on the remaining channels. The output-enable input (OE) is used to disable the outputs so the buses are effectively isolated. The OE_A pin is referenced to V_{CCA} and OE_B pin is referenced to V_{CCB} . The OE pin can be left floating or externally pulled down to ground to keep the translator outputs in a high-impedance state during power-up or power-down.

The V_{CC} disconnect feature ensures that if V_{CC} is disconnected with the complementary supply within recommended operating conditions, outputs are disabled and set to the high-impedance state while the supply current is maintained. The $I_{off-float}$ circuitry ensures that no excessive current is drawn from or sourced into an input or output while the supply is floating.

Glitch-free power supply sequencing allows either supply rail to be powered on or off in any order while providing robust power sequencing performance.

7.2 Functional Block Diagram

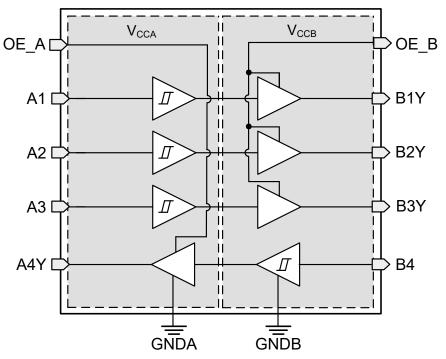


Figure 7-1. TXG804x-Q1 Functional Block Diagram



7.3 Feature Description

7.3.1 CMOS Schmitt-Trigger Inputs with Integrated Pulldowns

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the Section 5.5. The worst case resistance is calculated with the maximum input voltage, given in the Section 5.1, and the maximum input leakage current, given in the Section 5.5, using ohm's law (R = $V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the Section 5.5, which makes this device extremely tolerant to slow or noisy inputs. Driving the inputs slowly will increase dynamic current consumption of the device. See Understanding Schmitt Triggers for additional information regarding Schmitt-trigger inputs.

7.3.1.1 Inputs with Integrated Static Pull-Down Resistors

This device has $5M\Omega$ typical integrated weak pull-downs for each input. This feature allows all inputs to be left floating without the concern for unstable outputs or increased current consumption. This also helps to reduce external component count for applications where not all channels are used or need to be fixed low. If an external pull-up is required, it should be no larger than $1M\Omega$ to avoid contention with the $5M\Omega$ internal pull-down.

7.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. *Section 5.1* defines the electrical and thermal limits that must be followed at all times.

7.3.3 V_{CC} Disconnect

The outputs for this device are disabled and enter a high-impedance state when either supply is left floating (disconnected), and with the complementary supply within recommended operating conditions. It is recommended that the inputs are kept low before floating (disconnecting) either supply.

The $I_{CCx(floating)}$ in the Section 5.5 specifies the maximum supply current. The $I_{off(float)}$ in the Section 5.5 specifies the maximum leakage into or out of any input or output pin on the device.

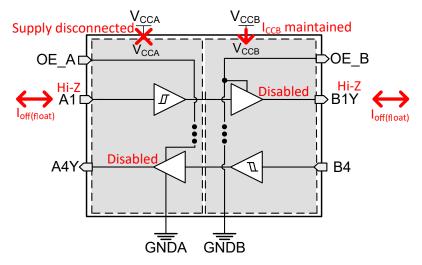


Figure 7-2. V_{CC} Disconnect Feature

7.3.4 Over-Voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Section 5.3*.



7.3.5 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the inputs or outputs (that is, where the output erroneously transitions to V_{CC} when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

7.3.6 Negative Clamping Diodes

Figure 7-3 depicts the inputs and outputs to this device that have negative clamping diodes.

CAUTION

Voltages beyond the values specified in the Section 5.1 table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

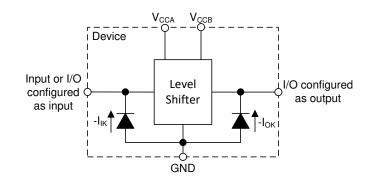


Figure 7-3. Electrical Placement of Clamping Diodes for Each Input and Output

7.3.7 Fully Configurable Dual-Rail Design

The V_{CCA} and V_{CCB} pins can be supplied at any voltage from 1.71V to 5.5V, making the device suitable for translating between any of the voltage nodes (1.8V, 2.5V, 3.3V, and 5.0V).

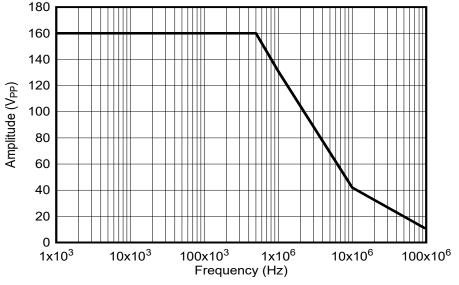
7.3.8 Supports High-Speed Translation

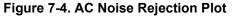
The TXG804x-Q1 device can support high data-rate applications. The translated signal data rate can be greater than 250Mbps when the signal is translated from 1.71V to 5.5V.

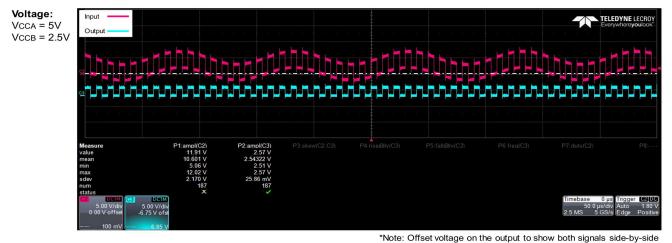


7.3.9 AC Noise Rejection

TXG804x-Q1 supports I/O voltage translation in environments with noisy grounds. The plot below illustrates the amount of noise that GNDA and GNDB can reject in terms peak-to-peak voltage over frequency without disrupting communication between two systems. As an example, Figure 7-5 below shows GNDA with a ground bounce of 2V_{PP} at 10kHz but still effectively translating 5V to 2.5V without any degradation.













7.4 Device Functional Modes

Table 7-1. Function Table

Power Supply		Control Inputs	Port S	tatus
VCCI	VCCO	OE	Input	Output
PU	PU	Н	н	Н
PU	PU	Н	L	L
PU	PU	L or Open	Х	Hi-Z
PU	PU	Н	Open	L
PD	PU	Н	X	L
Х	PU	L or Open	X	High-Z
Х	PU	Н	X	L
Х	PD	Х	X	Undetermined

 In the table above: PU = Powered Up; PD = Powered Down; X = Irrelevant; H = High Level; L = Low Level; Open = Floating



8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TXG804x-Q1 is used for level translation, enabling communication between devices or systems operating at different interface and ground voltages. The TXG804x-Q1 device is ideal for use in applications where a push-pull driver is connected to the data inputs. Figure 8-1 is an example of two systems that translate from 1.8V to 3.3V across a SPI interface while also seeing a ground shift of -5V on GNDB while GNDA is at 0V. The ground shift occurs due to the parasitic resistance of the cable used to connect the 48V battery ground and 12V battery ground to the chassis of the car.

8.2 Typical Application

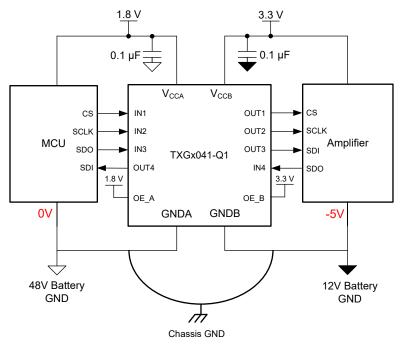


Figure 8-1. TXG804x-Q1 in Automotive

8.2.1 Design Requirements

Use the parameters listed in Table 8-1 for this design example.

Table 8-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUES			
Input voltage range	1.71V to 5.5V			
Output voltage range	1.71V to 5.5V			

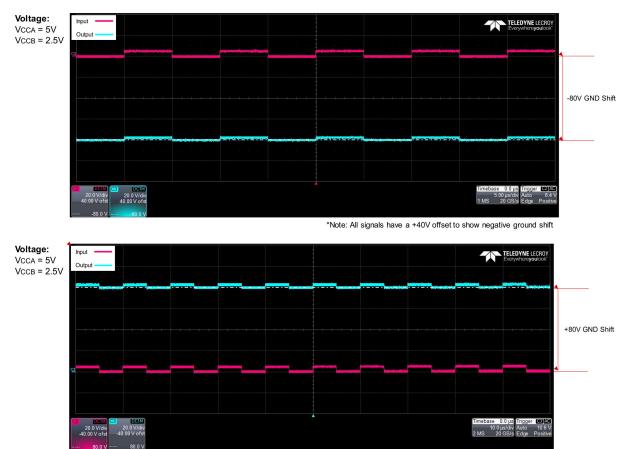
8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

Input voltage range



- Use the supply voltage of the device that is driving the TXG804x-Q1 device to determine the input voltage range. For a valid logic-high, the value must exceed the positive-going input-threshold voltage (V_{T+}) of the input port. For a valid logic low the value must be less than the negative-going input-threshold voltage (V_{T-}) of the input port.
- Output voltage range
 - Use the supply voltage of the device that the TXG804x-Q1 device is driving to determine the output voltage range.



8.2.3 Application Curves

*Note: All signals have a -40V offset to show positive ground shift

Figure 8-2. Waveform showing -80V (top) and +80V (bottom) Ground Shift with 5V to 2.5V I/O Translation



8.3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate. Please make sure the difference between V_{CC} and GND remains at 6.5V max at all times.

8.4 Layout

8.4.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines are recommended:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible. A 0.1µF capacitor is recommended, but transient performance can be improved by having 1µF and 0.1µF capacitors in parallel as bypass capacitors.
- The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing.
- A 0.1µF capacitor can be added between GNDA and GNDB to improve performances of CMTI.

8.4.2 Layout Example

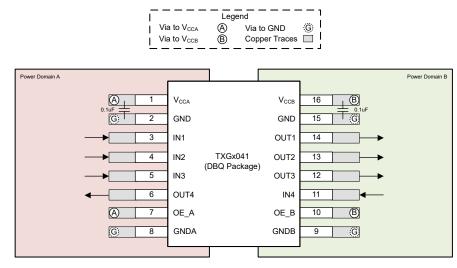


Figure 8-3. DBQ Layout Example



9 Device and Documentation Support

9.1 Device Support

9.1.1 Regulatory Requirements

No statutory or regulatory requirements apply to this device.

There are no special characteristics for this product.

9.2 Documentation Support

9.2.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Understanding Schmitt Triggers application report
- Texas Instruments, CMOS Power Consumption and C_{pd} Calculation application report

9.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.4 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.5 Trademarks

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9.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.7 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES		
May 2025	*	Initial APL Release		

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
PTXG8041QDBQRQ1	Active	Preproduction	SSOP (DBQ) 16	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
PTXG8041QDYYRQ1	Active	Preproduction	SOT-23-THIN (DYY) 14	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
PTXG8042QDBQRQ1	Active	Preproduction	SSOP (DBQ) 16	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
PTXG8042QDYYRQ1	Active	Preproduction	SOT-23-THIN (DYY) 14	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	

⁽¹⁾ **Status:** For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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DBQ0016A



PACKAGE OUTLINE

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- This dimension does not include interlead flash.
 Reference JEDEC registration MO-137, variation AB.



DBQ0016A

EXAMPLE BOARD LAYOUT

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBQ0016A

EXAMPLE STENCIL DESIGN

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.

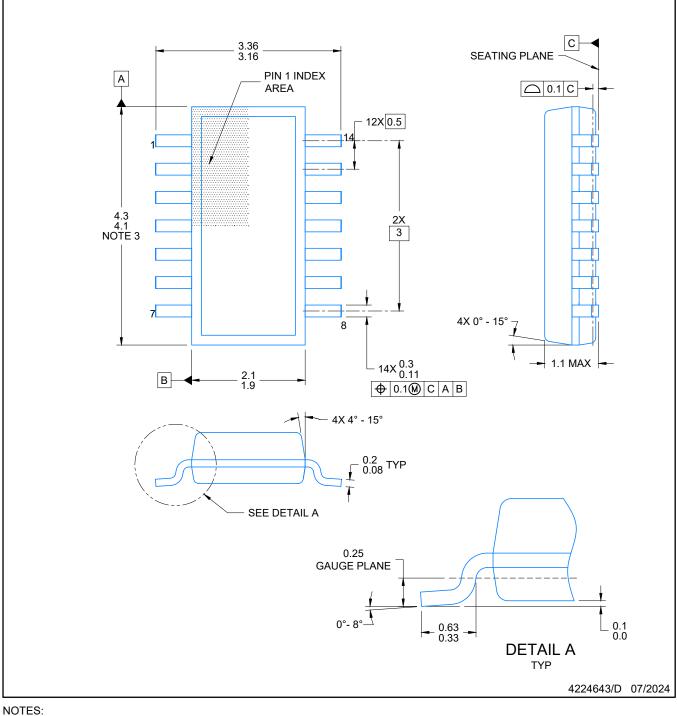


DYY0014A

PACKAGE OUTLINE

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



- IOTES.
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- 5. Reference JEDEC Registration MO-345, Variation AB

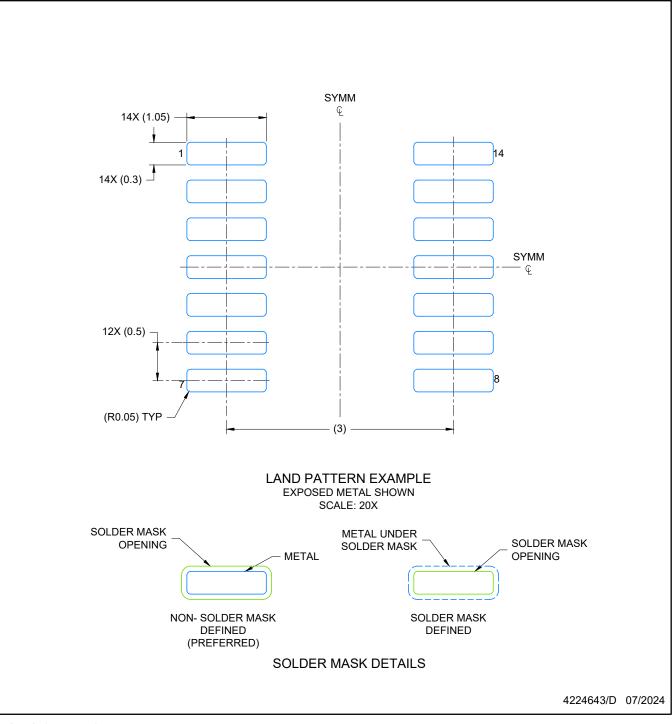


DYY0014A

EXAMPLE BOARD LAYOUT

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

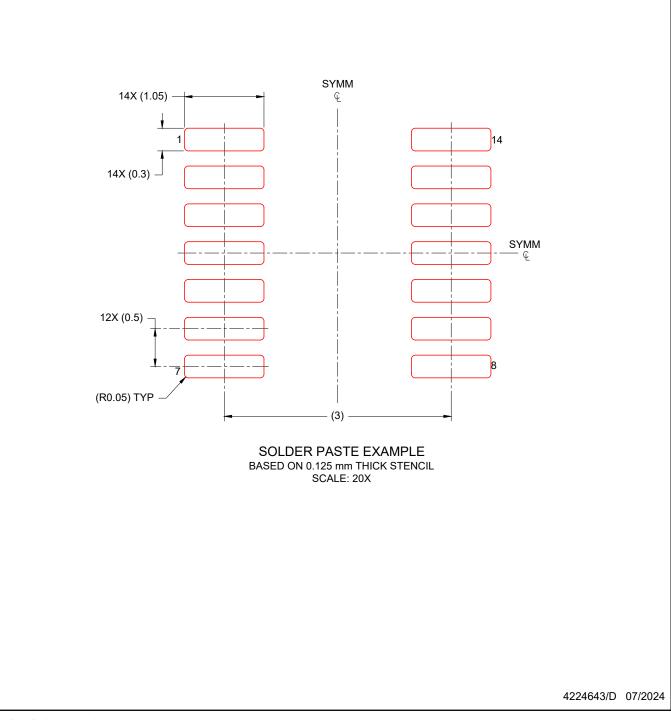


DYY0014A

EXAMPLE STENCIL DESIGN

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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